



MDD90N02G

20V N-Channel Enhancement Mode MOSFET

1. Description

This N-Channel MOSFET is produced using MDD Semiconductor's advanced Power Trench process technology. This process has been optimized to minimize on-state resistance and yet maintain superior switching performance with best in class soft body diode.

2. Features

- Max $R_{DS(on)}$ = 3.6 m Ω at V_{GS} = 4.5 V, I_D =30 A
- Extremely Low Reverse Recovery Charge, Q_{rr}
- 100% UIS Tested
- 100% dVDS Tested

3. Application

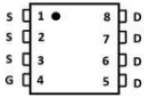
- Synchronous Rectification for ATX / Server / Telecom PSU
- Motor Drives and Uninterruptible Power Supplies
- DC-DC converters

4. Absolute Maximum Ratings($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current (Note 1)	I_D	90	A
Pulsed Drain Current (Note 2)	I_{DM}	360	A
Single Pulsed Avalanche Energy (Note 3)	E_{AS}	126.6	mJ
Thermal Resistance, steady-state	$R_{\theta JA}$	33	$^{\circ}\text{C}/\text{W}$
Junction Temperature	T_J	-55~+150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-55~+150	$^{\circ}\text{C}$

Note: 1) Calculated continuous current based on maximum allowable junction temperature.
2) Repetitive rating, pulse width limited by max. junction temperature.
3) E_{AS} condition : $T_J=25^{\circ}\text{C}$, $V_{DD}=20\text{V}$, $L=0.5\text{mH}$, $R_g=25\Omega$, $I_D=22.5\text{A}$

5. Pinning information

Pin	Symbol	Description	Simplified outline	Equivalent Circuit	Marking	Package
4	G	Gate			MDD 90N02G XXY: Date code	PDFN5*6-8L
5-8	D	Drain				
1-3	S	Source				

6. $T_A=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	20	—	—	V
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 12V$	—	—	± 100	nA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=20V, V_{GS}=0V$	—	—	1	μA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	0.45	—	0.95	V
$R_{DS(on)}$	Drain-Source On-State Resistance	$V_{GS}=4.5V, I_D=30A$	—	2.8	3.6	m Ω
		$V_{GS}=2.5V, I_D=20A$	—	3.9	4.9	m Ω

7. Dynamic Electrical Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS}=0V$ $V_{DS}=10V$ $f=1.0MHz$	—	3845	—	pF
C_{oss}	Output Capacitance		—	551	—	pF
C_{rss}	Reverse Transfer Capacitance		—	484	—	pF
Q_g	Total Gate Charge	$V_{GS}=0-8V$ $V_{DS}=10V$ $I_D=30A$	—	65	—	nC
Q_{gs}	Gate Source Charge		—	6	—	nC
Q_{gd}	Gate Drain Charge		—	16	—	nC

8. Switching Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$t_{d(on)}$	Turn on Delay Time	$V_{GS}=10V$ $V_{DD}=10V$ $I_D=30A$ $R_{\theta}=3\Omega$	—	8	—	ns
t_r	Turn on Rise Time		—	19	—	ns
$t_{d(off)}$	Turn Off Delay Time		—	73	—	ns
t_f	Turn Off Fall Time		—	80	—	ns

9. Source Drain Diode Characteristics

Symbol	Parameter	Condition		Typ	Max	Unit
V_{SD}	Drain-Source Diode Forward Voltage	$I_S=30A, V_{GS}=0V$	—	0.8	1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F=20A$	—	16	—	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$di/dt=100A/\mu s$	—	5.6	—	nC

10. Electrical Characteristics Diagrams

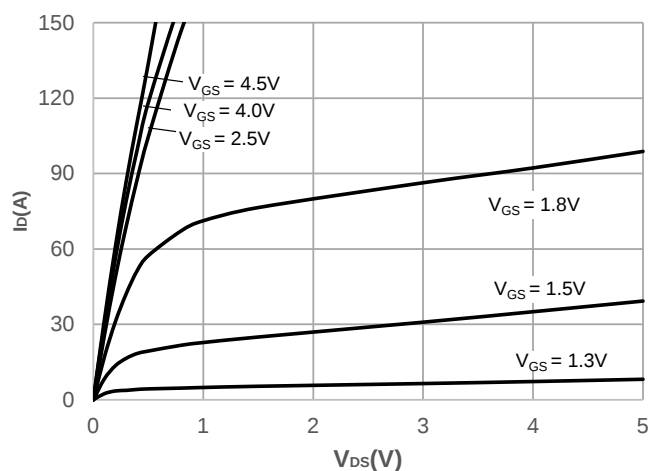


Figure 1. Typ. output characteristics

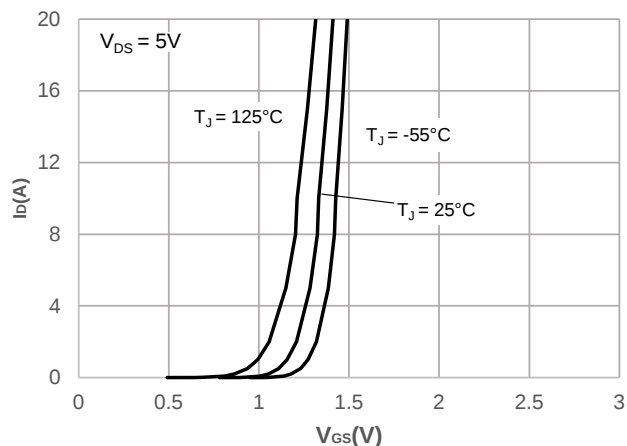


Figure 2. Typ. transfer characteristics

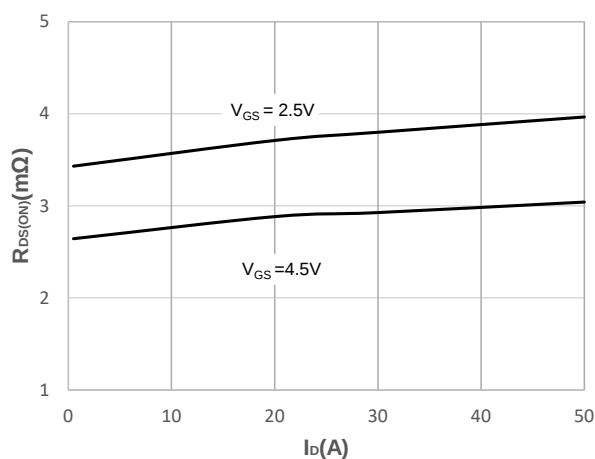


Figure 3. On-Resistance vs. Drain Current

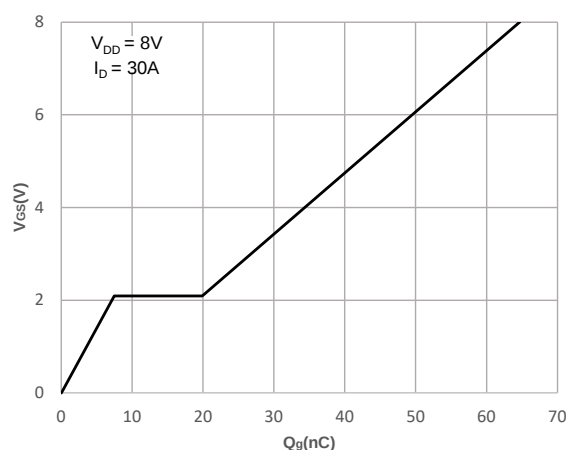


Figure 4. Gate Charge Characteristics

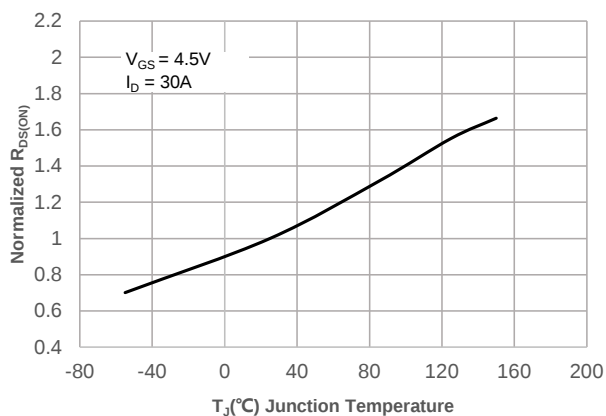


Figure 5. Normalized on Resistance vs. Junction Temperature

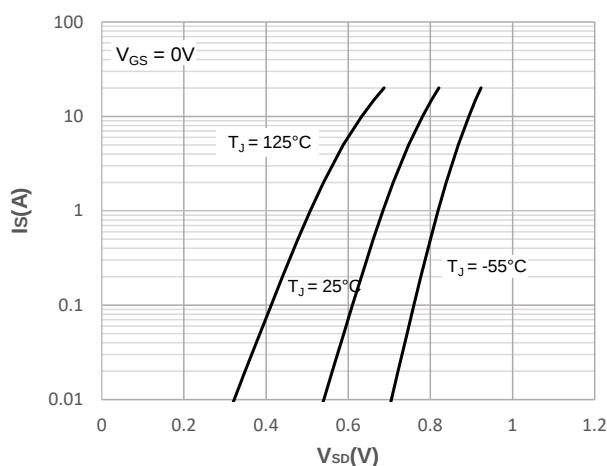


Figure 6. Forward characteristic of body diode

11. Test Circuits And Waveforms

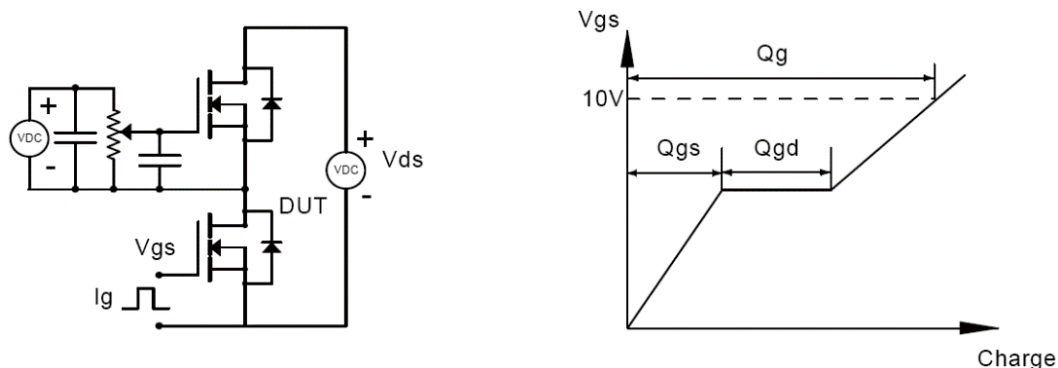


Figure 1. Gate charge test circuit & waveform

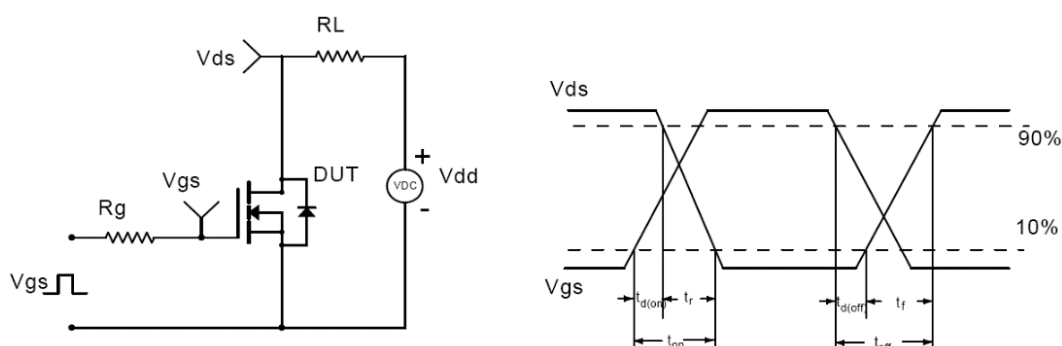


Figure 2. Switching time test circuit & waveforms

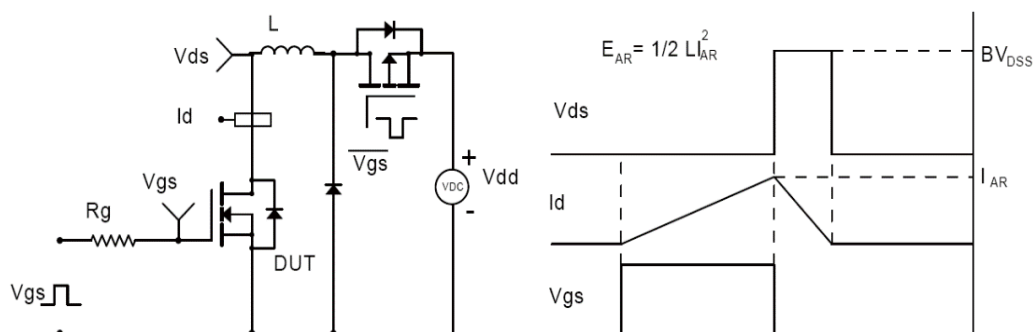


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

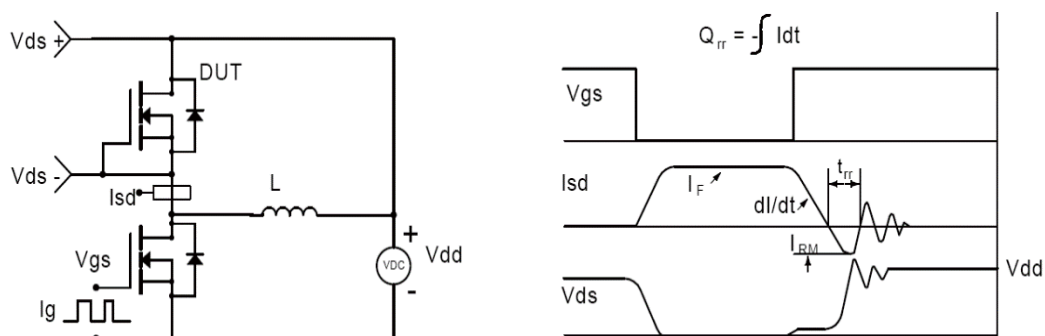
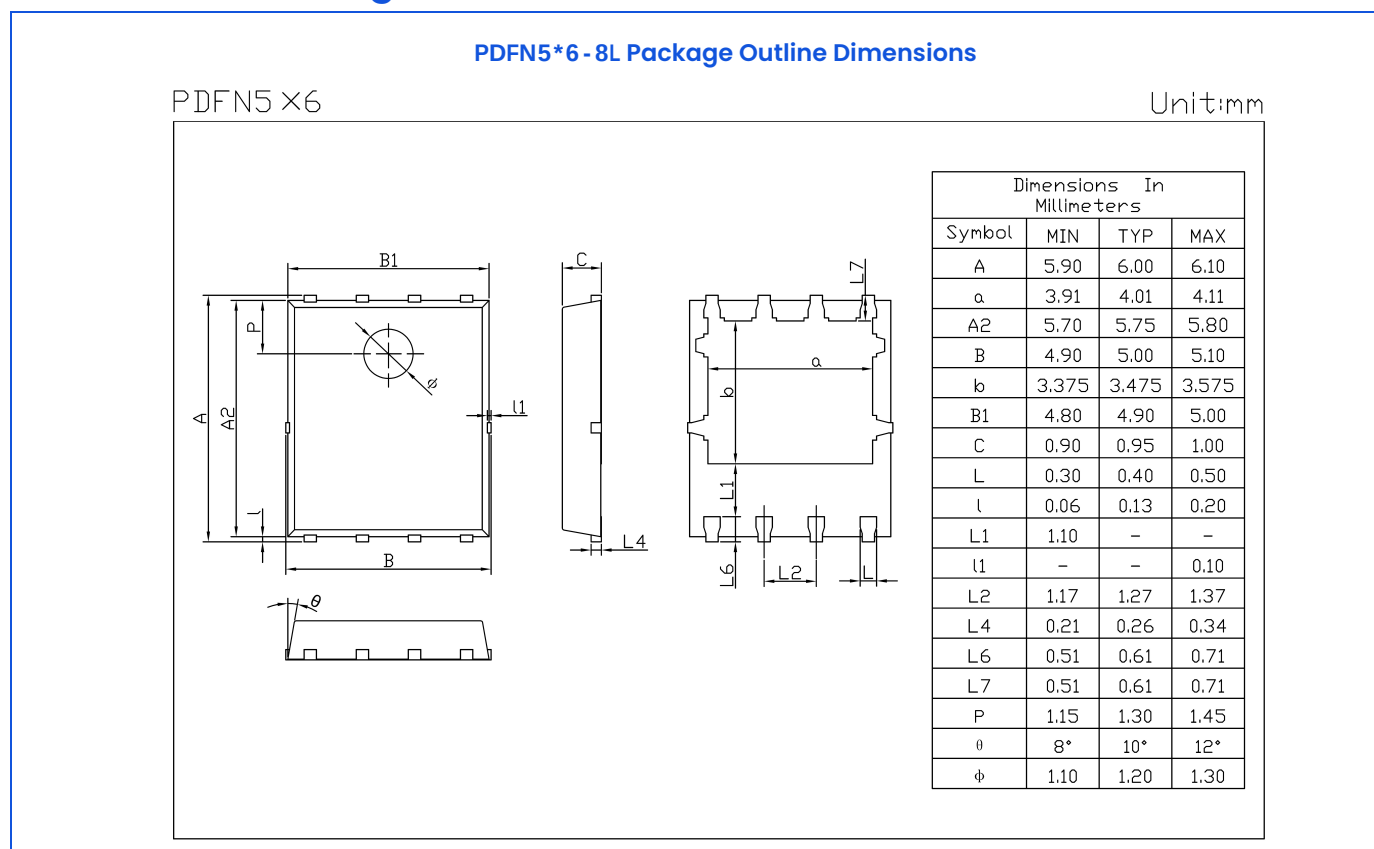


Figure 4. Diode reverse recovery test circuit & waveforms

12. Outline Drawing



13. Important Notice and Disclaimer

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